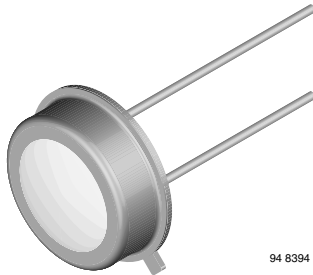


## Silicon Photodiode, RoHS Compliant



### DESCRIPTION

BPW21R is a planar Silicon PN photodiode in a hermetically sealed short TO-5 case, especially designed for high precision linear applications.

Due to its extremely high dark resistance, the short circuit photocurrent is linear over seven decades of illumination level.

On the other hand, there is a strictly logarithmic correlation between open circuit voltage and illumination over the same range.

The device is equipped with a flat glass window with built in color correction filter, giving an approximation to the spectral response of the human eye.

### FEATURES

- Package type: leaded
- Package form: TO-5
- Dimensions (in mm): Ø 8.13
- Radiant sensitive area (in mm<sup>2</sup>): 7.5
- High photo sensitivity
- Adapted to human eye responsivity
- Angle of half sensitivity:  $\varphi = \pm 50^\circ$
- Hermetically sealed package
- Cathode connected to package
- Flat glass window
- Low dark current
- High shunt resistance
- High linearity
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



**RoHS**  
COMPLIANT

### APPLICATIONS

- Sensor in exposure and color measuring purposes

### PRODUCT SUMMARY

COMPONENT	$I_{ra}$ (mA)	$\varphi$ (deg)	$\lambda_{0.5}$ (nm)
BPW21R	9	$\pm 50$	420 to 675

**Note**

Test condition see table "Basic Characteristics"

### ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
BPW21R	Bulk	MOQ: 500 pcs, 500 pcs/bulk	TO-5

**Note**

MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	10	V
Power dissipation	$T_{amb} \leq 50^\circ\text{C}$	$P_V$	300	mW
Junction temperature		$T_j$	125	$^\circ\text{C}$
Operating temperature range		$T_{amb}$	- 40 to + 125	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	- 40 to + 125	$^\circ\text{C}$
Soldering temperature	$t \leq 5\text{ s}$	$T_{sd}$	260	$^\circ\text{C}$
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm <sup>2</sup>	$R_{thJA}$	250	K/W

**Note**

$T_{amb} = 25^\circ\text{C}$ , unless otherwise specified

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 50 \text{ mA}$	$V_F$		1.0	1.3	V
Breakdown voltage	$I_R = 20 \text{ }\mu\text{A}, E = 0$	$V_{(BR)}$	10			V
Reverse dark current	$V_R = 5 \text{ V}, E = 0$	$I_{ro}$		2	30	nA
Diode capacitance	$V_R = 0 \text{ V}, f = 1 \text{ MHz}, E = 0$	$C_D$		1.2		nF
	$V_R = 5 \text{ V}, f = 1 \text{ MHz}, E = 0$	$C_D$		400		pF
Dark resistance	$V_R = 10 \text{ mV}$	$R_D$		38		$G\Omega$
Open circuit voltage	$E_A = 1 \text{ klx}$	$V_o$	280	450		mV
Temperature coefficient of $V_o$	$E_A = 1 \text{ klx}$	$TK_{V_o}$		-2		mV/K
Short circuit current	$E_A = 1 \text{ klx}$	$I_k$	4.5	9		$\mu\text{A}$
Temperature coefficient of $I_k$	$E_A = 1 \text{ klx}$	$TK_{I_k}$		-0.05		%/K
Reverse light current	$E_A = 1 \text{ klx}, V_R = 5 \text{ V}$	$I_{ra}$	4.5	9		$\mu\text{A}$
Sensitivity	$V_R = 5 \text{ V}, E_A = 10^{-2} \text{ to } 10^5 \text{ lx}$	$S$		9		nA/lx
Angle of half sensitivity		$\varphi$		$\pm 50$		deg
Wavelength of peak sensitivity		$\lambda_p$		565		nm
Range of spectral bandwidth		$\lambda_{0.5}$		420 to 675		nm
Rise time	$V_R = 0 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 660 \text{ nm}$	$t_r$		3.1		$\mu\text{s}$
Fall time	$V_R = 0 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 660 \text{ nm}$	$t_f$		3.0		$\mu\text{s}$

**Note**

$T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified

**BASIC CHARACTERISTICS**

$T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified

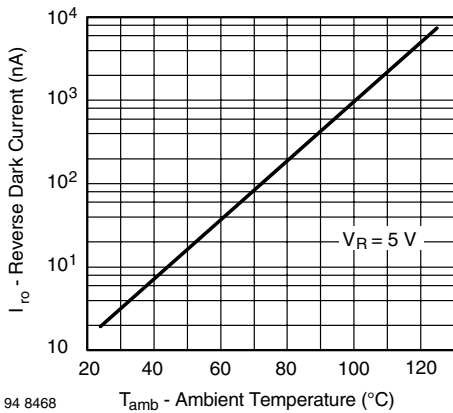


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

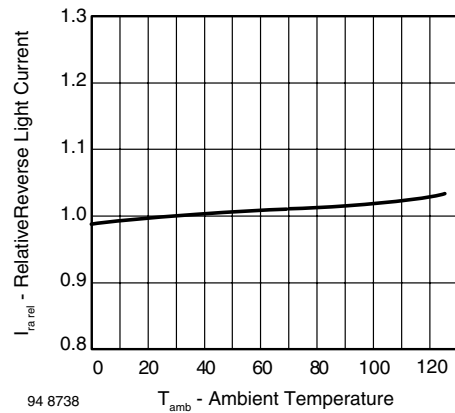
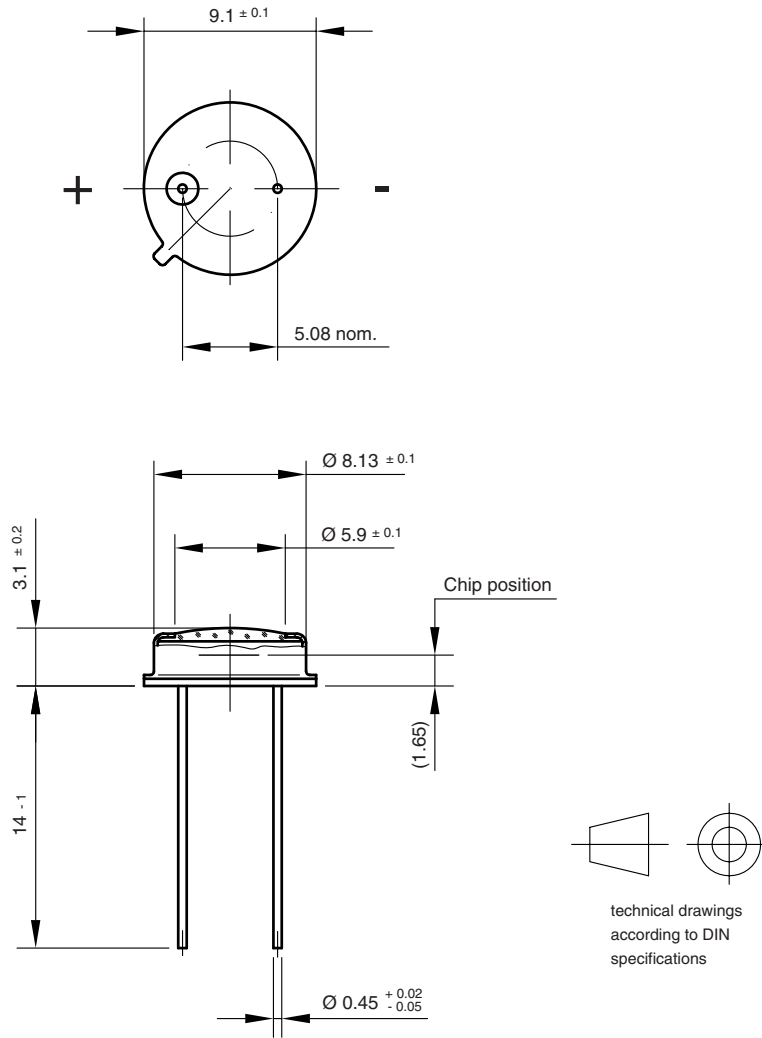


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

**PACKAGE DIMENSIONS** in millimeters



Drawing-No.: 6.511-5002.01-4  
Issue:1; 01.07.96  
96 12181